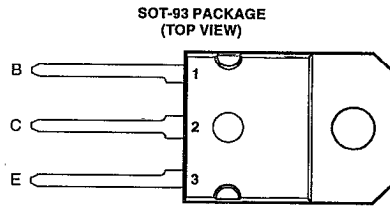


TIP33, TIP33A, TIP33B, TIP33C NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

- Designed for Complementary Use with the TIP34 Series
- 80 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP33	V_{CBO}	80	V
	TIP33A		100	
	TIP33B		120	
	TIP33C		140	
Collector-emitter voltage ($I_B = 0$)	TIP33	V_{CEO}	40	V
	TIP33A		60	
	TIP33B		80	
	TIP33C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	10	A
Peak collector current (see Note 1)		I_{CM}	15	A
Continuous base current		I_B	3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	62.5	mJ
Operating junction temperature range		T_J	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_B = 0.1 \Omega$, $V_{CC} = 20$ V.

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TIP33, TIP33A, TIP33B, TIP33C
NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5)	$I_B = 0$	TIP33	40		V
				TIP33A	60		
				TIP33B	80		
				TIP33C	100		
I_{CES}	Collector-emitter cut-off current	$V_{CE} = 80 \text{ V}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 120 \text{ V}$ $V_{CE} = 140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP33		0.4	mA
				TIP33A		0.4	
				TIP33B		0.4	
				TIP33C		0.4	
I_{CEO}	Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIP33/33A		0.7	mA
				TIP33B/33C		0.7	
I_{EBO}	Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$			1	mA
h_{FE}	Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$ $I_C = 3 \text{ A}$	(see Notes 5 and 6)	40		
					20		
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 0.3 \text{ A}$ $I_B = 2.5 \text{ A}$	$I_C = 3 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)		1	V
						4	
V_{BE}	Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 3 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)		1.6	V
						3	
h_{fe}	Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	20		
$ h_{fe} $	Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	3		

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

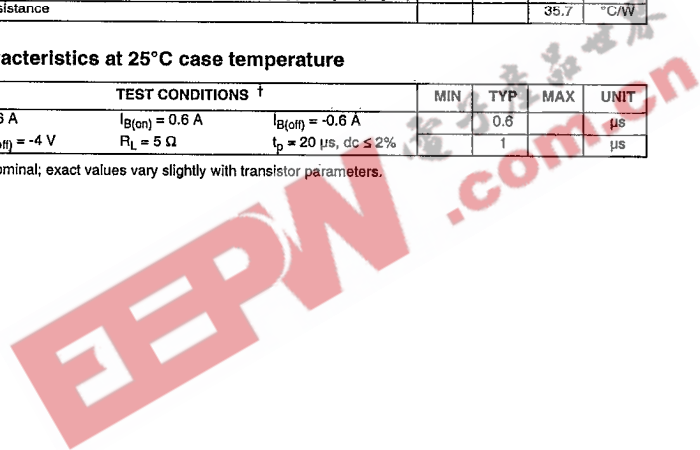
thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.56	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †		MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	$I_C = 6 \text{ A}$	$I_{B(on)} = 0.6 \text{ A}$		0.6		μs
t_{off}	Turn-off time	$V_{BE(off)} = -4 \text{ V}$	$R_L = 5 \Omega$		1		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TIP33, TIP33A, TIP33B, TIP33C
NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT

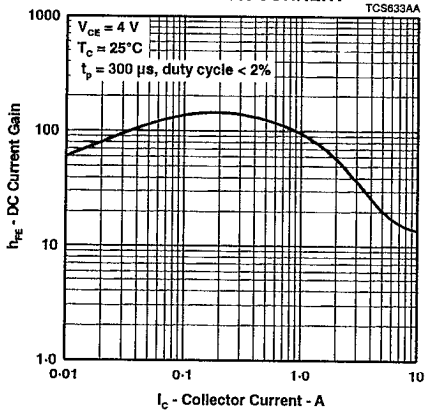


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT

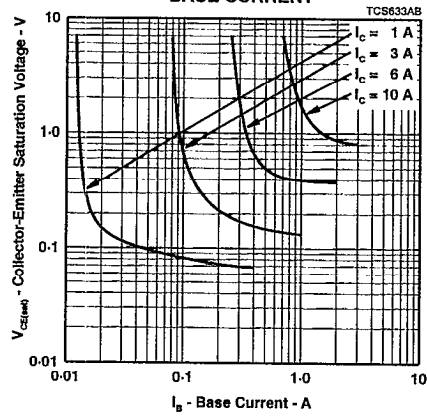


Figure 2.

BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

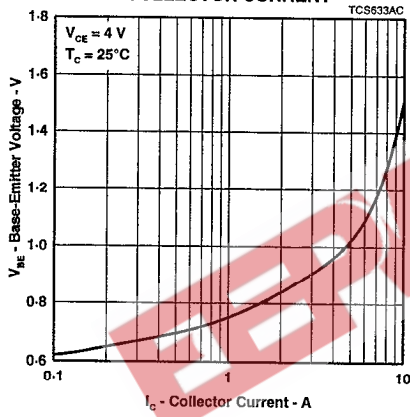


Figure 3.

TIP33, TIP33A, TIP33B, TIP33C
NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

MAXIMUM SAFE OPERATING REGIONS

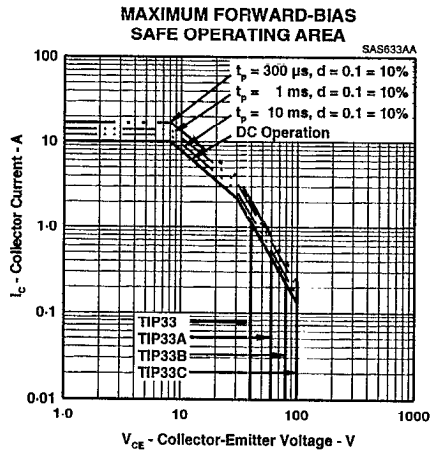


Figure 4.

THERMAL INFORMATION

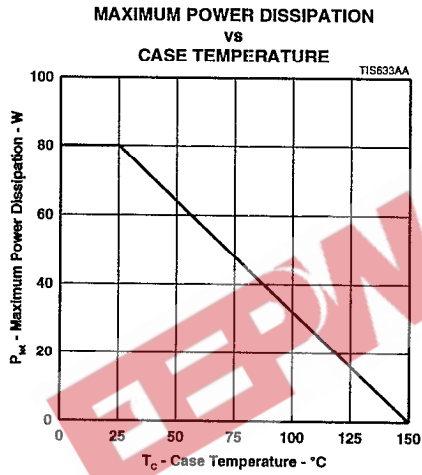


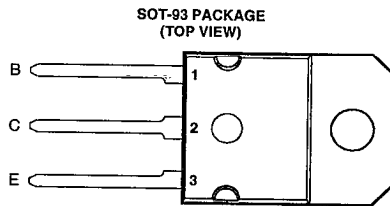
Figure 5.

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TIP34, TIP34A, TIP34B, TIP34C PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

- Designed for Complementary Use with the TIP33 Series
- 80 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP34	V_{CBO}	-80	V
	TIP34A		-100	
	TIP34B		-120	
	TIP34C		-140	
Collector-emitter voltage ($I_B = 0$)	TIP34	V_{CEO}	-40	V
	TIP34A		-60	
	TIP34B		-80	
	TIP34C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-10	A
Peak collector current (see Note 1)		I_{CM}	-15	A
Continuous base current		I_B	-3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	62.5	mJ
Operating junction temperature range		T_J	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = -0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(on)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20$ V.

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TIP34, TIP34A, TIP34B, TIP34C
PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ (see Note 5)	$I_B = 0$	TIP34 TIP34A TIP34B TIP34C	-40 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$ $V_{CE} = -120 \text{ V}$ $V_{CE} = -140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP34 TIP34A TIP34B TIP34C			-0.4 -0.4 -0.4 -0.4	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIP34/34A TIP34B/34C			-0.7 -0.7	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$ $I_C = -3 \text{ A}$	(see Notes 5 and 6)	40 20		100	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -0.3 \text{ A}$ $I_B = -2.5 \text{ A}$	$I_C = -3 \text{ A}$ $I_C = -10 \text{ A}$	(see Notes 5 and 6)			-1 -4	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -3 \text{ A}$ $I_C = -10 \text{ A}$	(see Notes 5 and 6)			-1.6 -3	V
h_{ie} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{ie} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

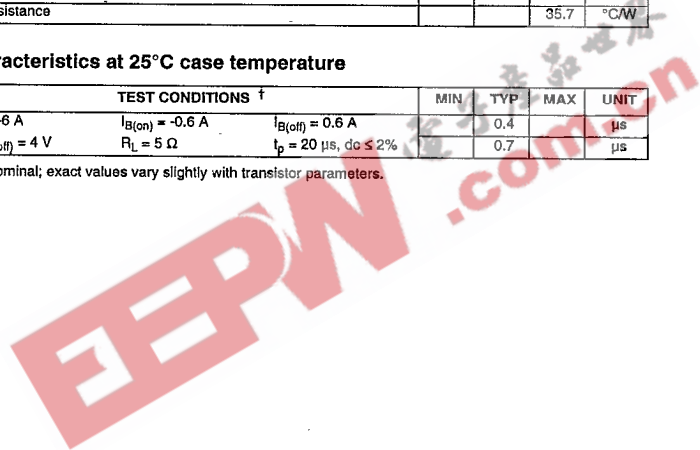
thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.56	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -6 \text{ A}$	$I_{B(on)} = -0.6 \text{ A}$	$I_{B(off)} = 0.6 \text{ A}$		0.4		μs
t_{off} Turn-off time	$V_{BE(off)} = 4 \text{ V}$	$R_L = 5 \Omega$	$t_p = 20 \mu\text{s}$, $d_c \leq 2\%$		0.7		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TIP34, TIP34A, TIP34B, TIP34C
PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

TYPICAL CHARACTERISTICS

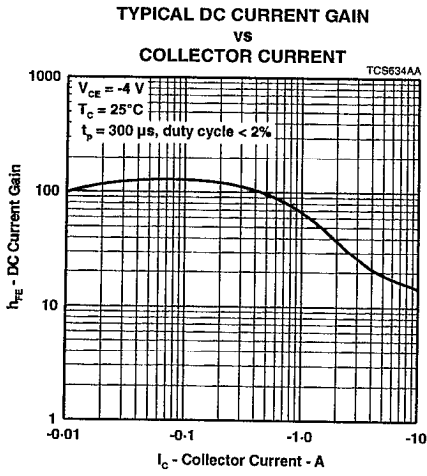


Figure 1.

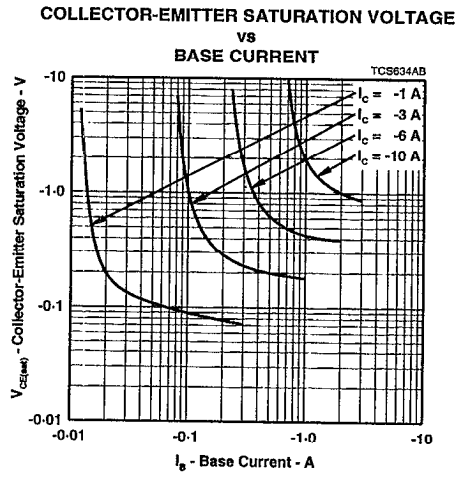


Figure 2.

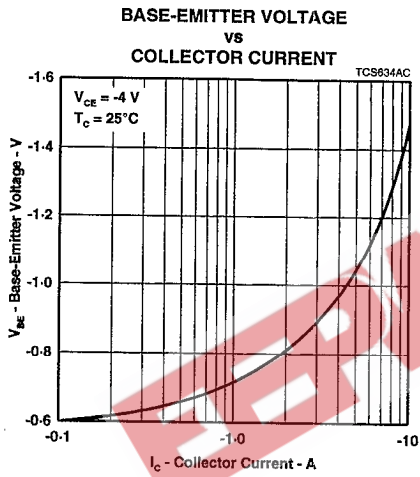


Figure 3.

TIP34, TIP34A, TIP34B, TIP34C
PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

MAXIMUM SAFE OPERATING REGIONS

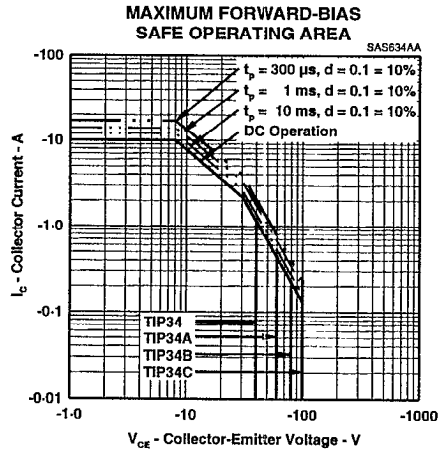


Figure 4.

THERMAL INFORMATION

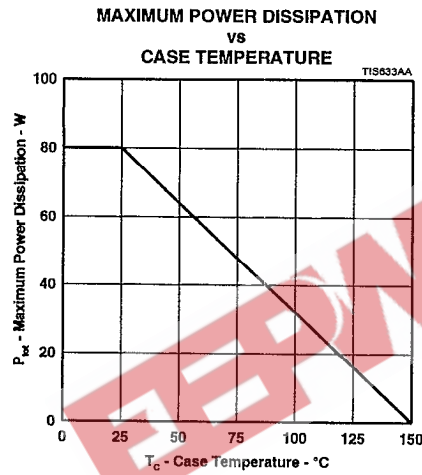


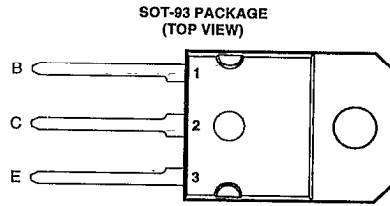
Figure 5.

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TIP35, TIP35A, TIP35B, TIP35C NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

- Designed for Complementary Use with the TIP36 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP35	V_{CBO}	80	V
	TIP35A		100	
	TIP35B		120	
	TIP35C		140	
Collector-emitter voltage ($I_B = 0$)	TIP35	V_{CEO}	40	V
	TIP35A		60	
	TIP35B		80	
	TIP35C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	25	A
Peak collector current (see Note 1)		I_{CM}	40	A
Continuous base current		I_B	5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating junction temperature range		T_J	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

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TIP35, TIP35A, TIP35B, TIP35C
NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5)	$I_B = 0$	TIP35 TIP35A TIP35B TIP35C	40 60 80 100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = 80 \text{ V}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 120 \text{ V}$ $V_{CE} = 140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP35 TIP35A TIP35B TIP35C			0.7 0.7 0.7 0.7	mA
I_{CEO} Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIP35/35A TIP35B/35C			1 1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 1.5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)	25 10		50	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 1.5 \text{ A}$ $I_B = 5 \text{ A}$	$I_C = 15 \text{ A}$ $I_C = 25 \text{ A}$	(see Notes 5 and 6)			1.8 4	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 15 \text{ A}$ $I_C = 25 \text{ A}$	(see Notes 5 and 6)			2 4	V
h_{ie} Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ kHz}$	25			
$ h_{ie} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 15 \text{ A}$	$I_{B(on)} = 1.5 \text{ A}$	$I_{B(off)} = -1.5 \text{ A}$		1.2		μs
t_{off} Turn-off time	$V_{BE(off)} = -4.15 \text{ V}$	$R_L = 2 \Omega$	$t_p = 20 \mu\text{s}$, $d_c \leq 2\%$		0.9		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TIP35, TIP35A, TIP35B, TIP35C
NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

TYPICAL CHARACTERISTICS

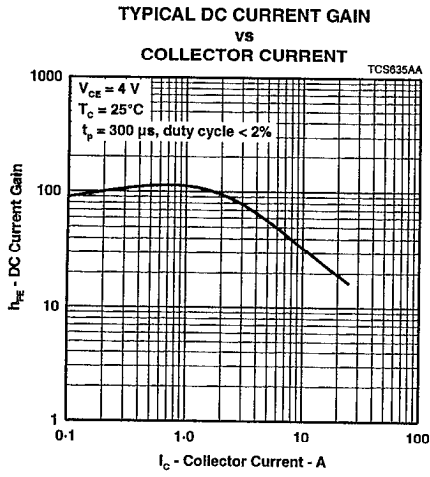


Figure 1.

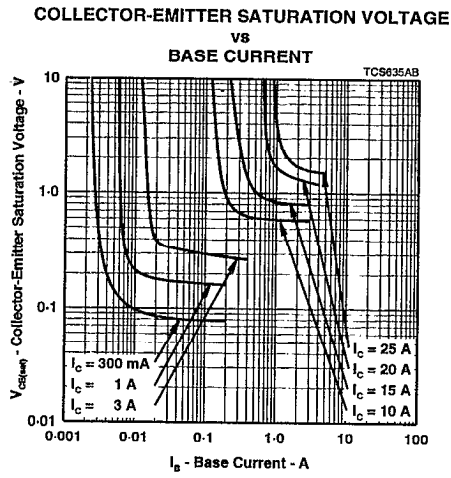


Figure 2.

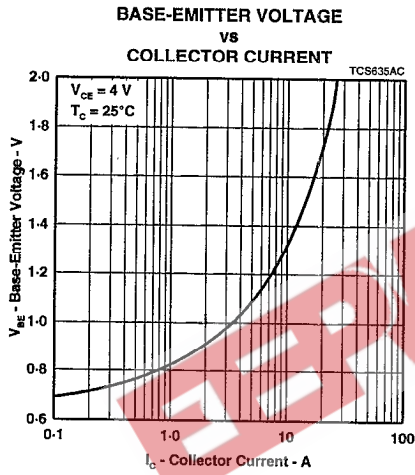


Figure 3.

TIP35, TIP35A, TIP35B, TIP35C
 NPN SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

MAXIMUM SAFE OPERATING REGIONS

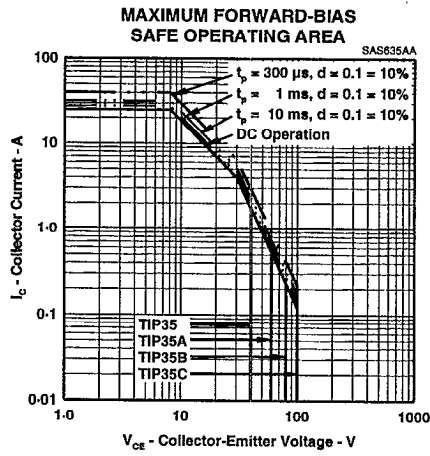


Figure 4.

THERMAL INFORMATION

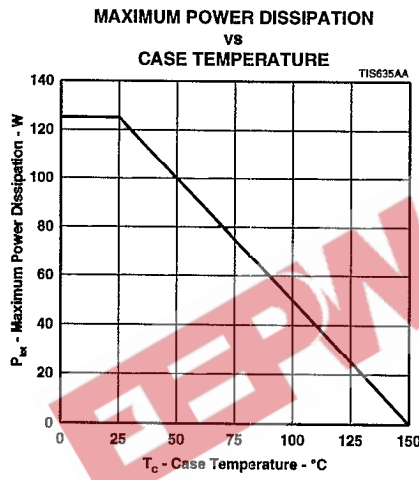


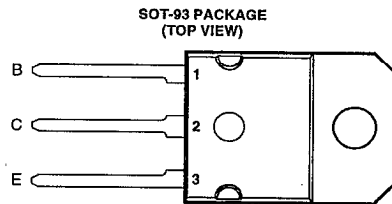
Figure 5.

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TIP36, TIP36A, TIP36B, TIP36C PNP SILICON POWER TRANSISTORS

JULY 1968 - REVISED MAY 1995

- Designed for Complementary Use with the TIP35 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP36	V_{CBO}	-80	V
	TIP36A		-100	
	TIP36B		-120	
	TIP36C		-140	
Collector-emitter voltage ($I_B = 0$)	TIP36	V_{CEO}	-40	V
	TIP36A		-60	
	TIP36B		-80	
	TIP36C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-25	A
Peak collector current (see Note 1)		I_{CM}	-40	A
Continuous base current		I_B	-5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating junction temperature range		T_J	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = -0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(on)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20$ V.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all the parameters.



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TIP36, TIP36A, TIP36B, TIP36C PNP SILICON POWER TRANSISTORS

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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30$ mA (see Note 5)	$I_B = 0$	TIP36 TIP36A TIP36B TIP36C	-40 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -80$ V $V_{CE} = -100$ V $V_{CE} = -120$ V $V_{CE} = -140$ V	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP36 TIP36A TIP36B TIP36C			-0.7 -0.7 -0.7 -0.7	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30$ V $V_{CE} = -60$ V	$I_B = 0$ $I_B = 0$	TIP36/36A TIP36B/36C			-1 -1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5$ V	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4$ V $V_{CE} = -4$ V	$I_C = -1.5$ A $I_C = -15$ A	(see Notes 5 and 6)	25 10		50	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -1.5$ A $I_B = -5$ A	$I_C = -15$ A $I_C = -25$ A	(see Notes 5 and 6)			-1.8 -4	V
V_{BE} Base-emitter voltage	$V_{CE} = -4$ V $V_{CE} = -4$ V	$I_C = -15$ A $I_C = -25$ A	(see Notes 5 and 6)			-2 -4	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10$ V	$I_C = -1$ A	$f = 1$ kHz	25			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10$ V	$I_C = -1$ A	$f = 1$ MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300$ μ s, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

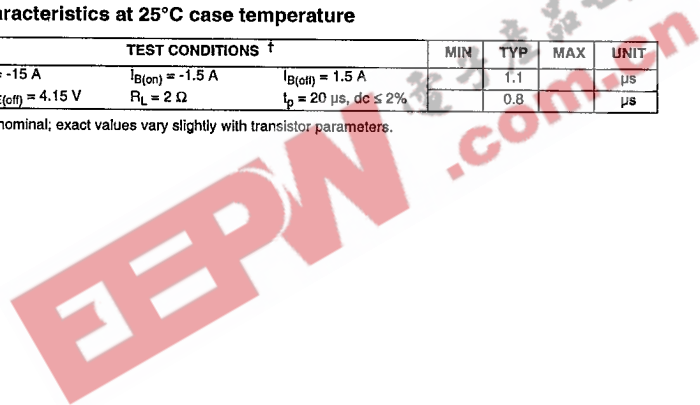
thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -15$ A	$I_{B(on)} = -1.5$ A	$I_{B(off)} = 1.5$ A		1.1		μ s
t_{off} Turn-off time	$V_{BE(off)} = 4.15$ V	$R_L = 2$ Ω	$t_p = 20$ μ s, $d_c \leq 2\%$		0.8		μ s

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TIP36, TIP36A, TIP36B, TIP36C
PNP SILICON POWER TRANSISTORS

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TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT

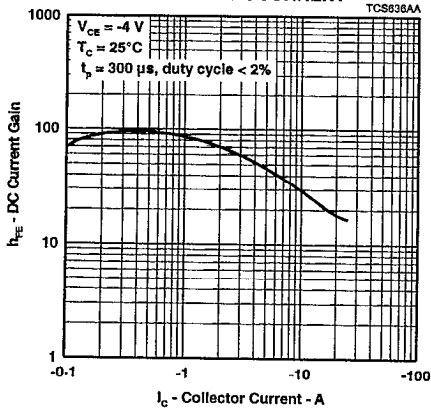


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT

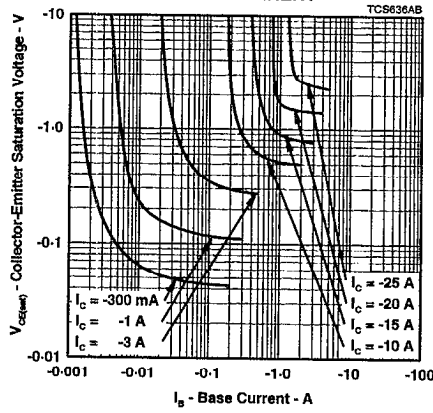


Figure 2.

BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

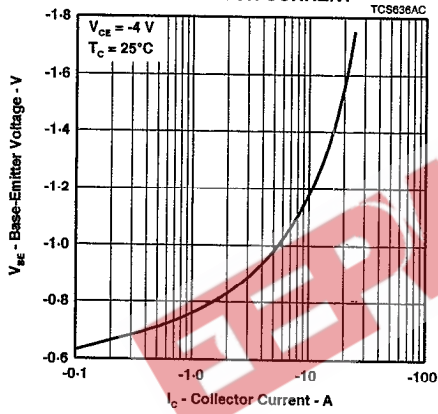


Figure 3.

TIP36, TIP36A, TIP36B, TIP36C
PNP SILICON POWER TRANSISTORS

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MAXIMUM SAFE OPERATING REGIONS

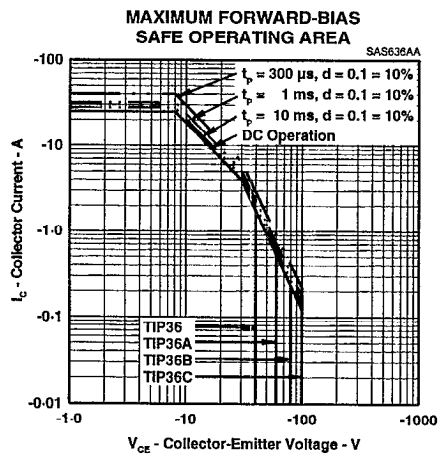


Figure 4.

THERMAL INFORMATION

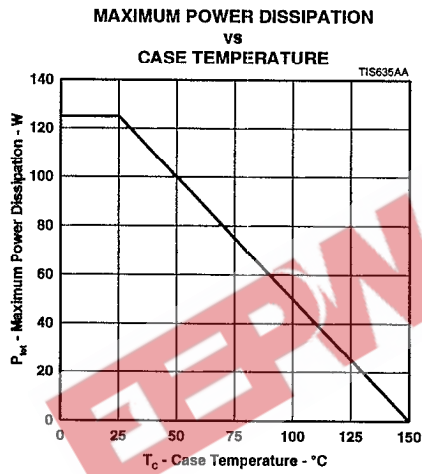


Figure 5.

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